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11	NFORMATION DISC	CLC	SURE	Filing Date	11/26/2003		
	TATEMENT BY AF			First Named Inventor	TADAHIRO OHMI		
		. —		Art Unit	2818		
	(Use as many sheets as nec	essarv)	Examiner Name	David Vu		
Sheet	1	of	1	Attorney Docket Number	040258-0306947		

	1 64		U. S. PATENT		
Examiner Initials*	Cite No.1	Document Number Number-Kind Code ^{2 (d known)}	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
DV	1	US- 6,479,392	11-12-2002	YAMAZAKI et al.	
DV	2	US- 6,380,033	04-30-2002	HE et al.	
DV	3	US- 2001/0044187	11-22-2001	JOO et al.	
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	FOREIGN PATENT DOCUMENTS											
Examiner Initials*	Cite No. ¹		ratent Document de ³⁻ Number ⁴⁻ Kind Code ⁵ (// known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	Τ ⁶					
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	В	JP	59-105371	06-18-1984	KOMORI							
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DV	Е	JP	9-213820	08-15-1997	USHIYAMA et al.							

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STATEMENT BY APPLICANT				First Named Inventor	TADAHIRO OHMI			
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	NON PATENT LITERATURE DOCUMENTS	
Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
A	ITO ET AL., "Silicon Oxynitridation With Inductively Coupled Oxygen-Nitrogen Mixed Plasma," Japan J. Appl. Phys., p. 612-616, (1997).	
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С	SAITO ET AL., "Low Temperature Formation of Gate-Grade Silicon Nitride Film Employing Microwave-Excitation High-Density Plasma," Technical Report of IEICE, p. 85-90, (1999).	
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